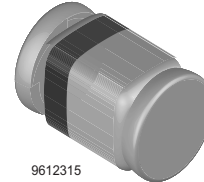


Small Signal Schottky Diodes

Features

- Integrated protection ring against static discharge
- Low capacitance
- Low leakage current
- Low forward voltage drop
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



9612315

Applications

- IHF-Detector
- Protection circuit
- Small battery charger
- AC-DC / DC-DC converters

Mechanical Data

Case: MicroMELF Glass case

Weight: approx. 12 mg

Cathode Band Color: Black

Packaging Codes/Options:

GS18 / 10 k per 13" reel (8 mm tape), 10 k/box

GS08 / 2.5 k per 7" reel (8 mm tape), 12.5 k/box

Parts Table

Part	Type differentiation	Ordering code	Remarks
MCL103A	$V_R = 40\text{ V}$, V_F at I_F 20 mA max. 0.37 V	MCL103A-GS18 or MCL103A-GS08	Tape and Reel
MCL103B	$V_R = 30\text{ V}$, V_F at I_F 20 mA max. 0.37 V	MCL103B-GS18 or MCL103B-GS08	Tape and Reel
MCL103C	$V_R = 20\text{ V}$, V_F at I_F 20 mA max. 0.37 V	MCL103C-GS18 or MCL103C-GS08	Tape and Reel

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Reverse voltage		MCL103A	V_R	40	V
		MCL103B	V_R	30	V
		MCL103C	V_R	20	V
Peak forward surge current	$t_p = 300\text{ }\mu\text{s}$, square pulse		I_{FSM}	15	A
Power dissipation	$l = 4\text{ mm}$, $T_L = \text{constant}$		P_{tot}	400	mW

Thermal Characteristics

$T_{amb} = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Junction ambient	$l = 4\text{ mm}$, $T_L = \text{constant}$	R_{thJA}	250	K/W
Junction temperature		T_j	125	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 65 to + 150	$^\circ\text{C}$

Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Reverse Breakdown Voltage	I _R = 10 μA	MCL103A	V _{(BR)R}	40			V
		MCL103B	V _{(BR)R}	30			V
		MCL103C	V _{(BR)R}	20			V
Leakage current	V _R = 30 V	MCL103A	I _R			5	μA
	V _R = 20 V	MCL103B	I _R			5	μA
	V _R = 10 V	MCL103C	I _R			5	μA
Forward voltage drop	I _F = 20 mA		V _F			0.37	V
	I _F = 200 mA		V _F			0.6	V
Diode capacitance	V _R = 0 V, f = 1 MHz		C _D		50		pF
Reverse recovery time	I _F = I _R = 50 to 200 mA, recover to 0.1 I _R		t _{rr}		10		ns

Typical Characteristics

T_{amb} = 25 °C, unless otherwise specified

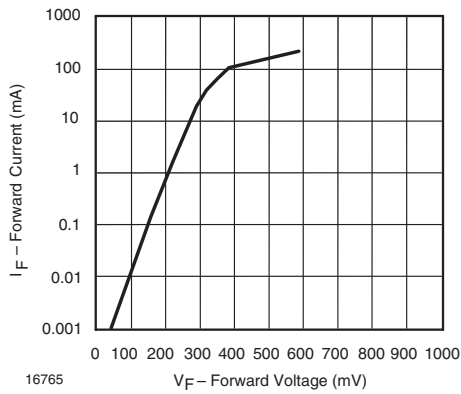


Figure 1. Forward Current vs. Forward Voltage

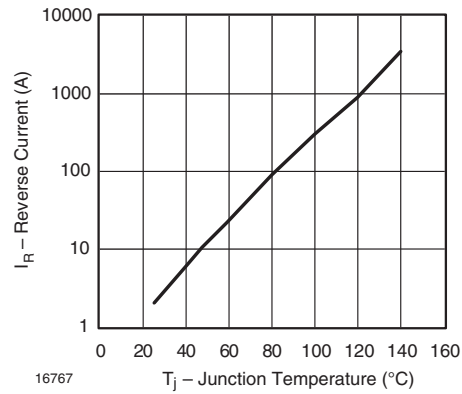


Figure 3. Reverse Current vs. Junction Temperature

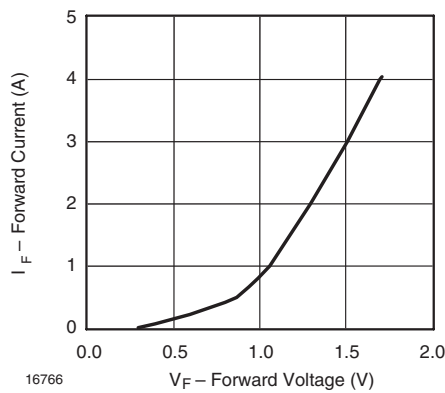


Figure 2. Forward Current vs. Forward Voltage

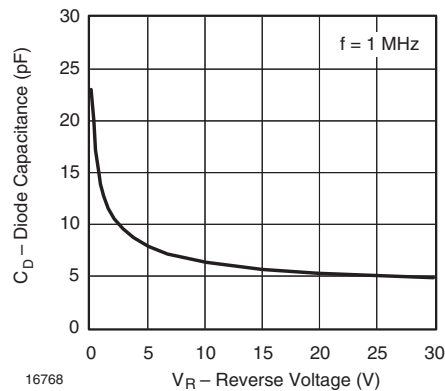


Figure 4. Diode Capacitance vs. Reverse Voltage

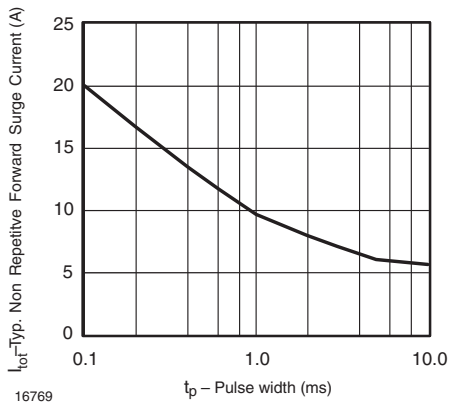
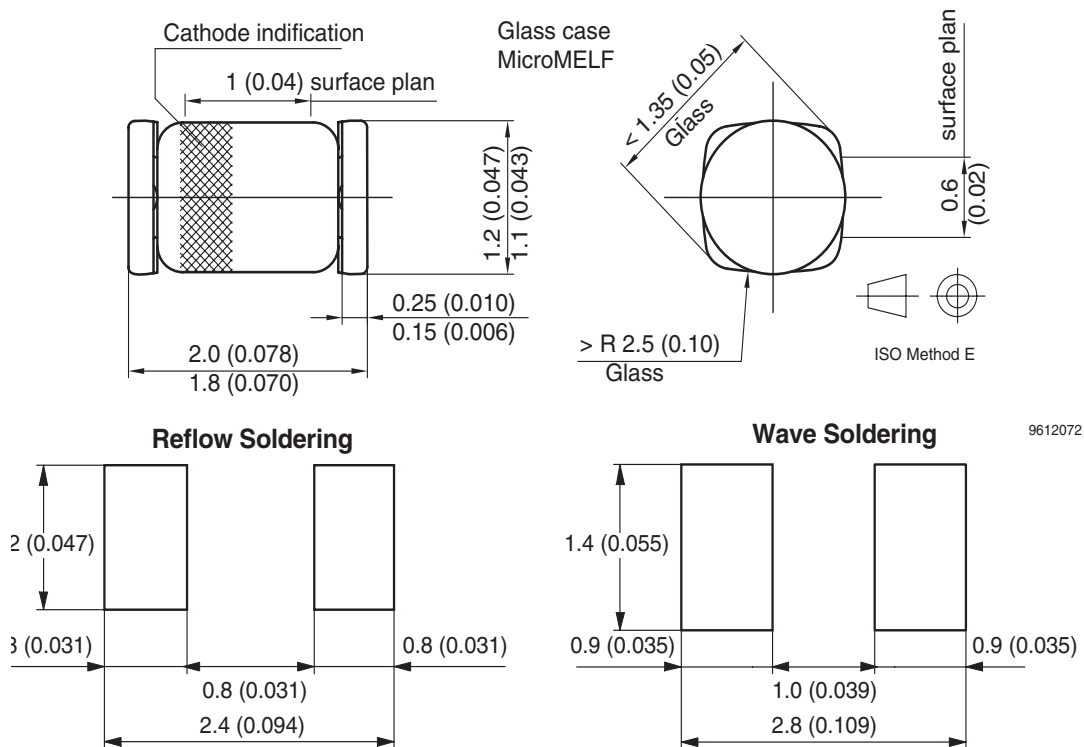


Figure 5. Typ. Non Repetitive Forward Surge Current vs. Pulse width

Package Dimensions in mm (Inches)



Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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